

GERMANIUM ALLOYED POWER TRANSISTOR

N-P-N power transistor in a metal envelope with the collector connected to the mounting base.

The AD161 is primarily intended for use together with the p-n-p power transistor AD162 as matched pair AD161/AD162 in 11 W complementary symmetry class B output stages of mains operated amplifiers and radio receivers.

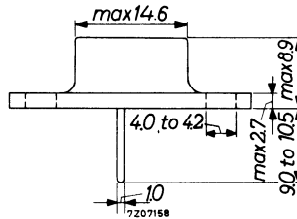
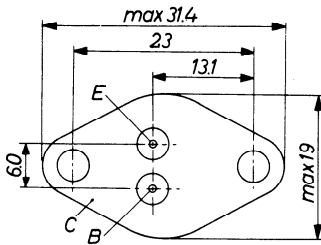


QUICK REFERENCE DATA		
Collector-base voltage (open emitter)	V_{CBO}	max. 32 V
Collector-emitter voltage (open base)	V_{CEO}	max. 20 V
Collector current (peak value)	I_{CM}	max. 3 A
Total power dissipation up to $T_{mb} = 75^{\circ}C$	P_{tot}	max. 4 W
Junction temperature (incidentally)	T_j	max. 100 $^{\circ}C$
D.C. current gain at $T_j = 25^{\circ}C$		
$I_C = 0.5 A; V_{CE} = 1 V$	h_{FE}	80 to 320
Cut-off frequency		
$I_C = 0.3 A; V_{CE} = 2 V$	f_{hfe}	typ. 35 kHz

MECHANICAL DATA

Dimensions in mm

Collector connected to mounting base



Accessories and mounting instructions see page 4.

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CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = 32\text{ V}$	I_{CBO}	typ.	20 μA
		<	500 μA
$I_E = 0; V_{CB} = 32\text{ V}; T_j = 90\text{ }^\circ\text{C}$	I_{CBO}	<	3 mA
$-V_{BE} = 0.6\text{ V}; V_{CE} = 32\text{ V}; T_j = 90\text{ }^\circ\text{C}$	I_{CEX}	<	3 mA

Emitter cut-off current

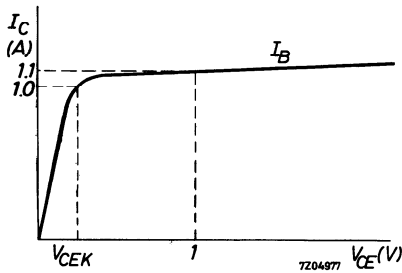
$I_C = 0; V_{EB} = 10\text{ V}$	I_{EBO}	typ.	20 μA
		<	200 μA
$I_C = 0; V_{EB} = 10\text{ V}; T_j = 90\text{ }^\circ\text{C}$	I_{EBO}	<	2 mA

Base-emitter voltage ¹⁾

$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}$	V_{BE}	110 to 140	mV
$I_C = 50\text{ mA}; V_{CE} = 1\text{ V}$	V_{BE}	<	300 mV
$I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	V_{BE}	<	650 mV
$I_C = 2\text{ A}; V_{CE} = 1\text{ V}$	V_{BE}	<	1100 mV ←

Knee voltage

$I_C = 1\text{ A}; I_B = \text{value for which}$			
$I_C = 1.1\text{ A at } V_{CE} = 1\text{ V}$	V_{CEK}	<	600 mV ←



Floating voltage

$I_E = 0; V_{CB} = 32\text{ V}; T_j = 90\text{ }^\circ\text{C}$	V_{EBfl}	<	400 mV
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Collector capacitance at $f = 450\text{ kHz}$

$I_E = I_e = 0; V_{CB} = 5\text{ V}$	C_c	typ.	150 pF
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¹⁾ V_{BE} decreases by about $2\text{ mV}/^\circ\text{C}$ with increasing temperature. 7Z3 0944

AD161

AD161/AD162

CHARACTERISTICS (continued)

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

→ D.C. current gain

$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}$	h_{FE}	>	55
$I_C = 50\text{ mA}; V_{CE} = 1\text{ V}$	h_{FE}		74 to 300
$I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	h_{FE}	typ.	150
			80 to 320
$I_C = 2\text{ A}; V_{CE} = 1\text{ V}$	h_{FE}	>	40

Transition frequency

$I_C = 10\text{ mA}; V_{CE} = 2\text{ V}$	f_T	typ.	3 MHz
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Cut-off frequency

$I_C = 300\text{ mA}; V_{CE} = 2\text{ V}$	f_{hfe}	>	20 kHz
		typ.	35 kHz

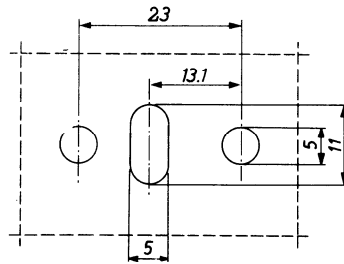
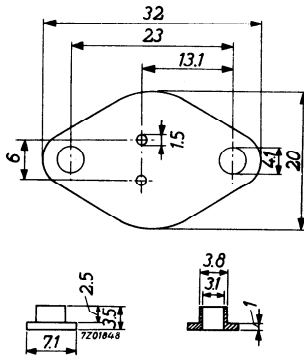
D.C. current gain ratio

of matched pair AD161/AD162

$I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	h_{FE1}/h_{FE2}	typ.	1.1
		<	1.25

ACCESSORIES AND MOUNTING INSTRUCTIONS

Dimensions in mm



Bore-hole dimensions
for heatsink

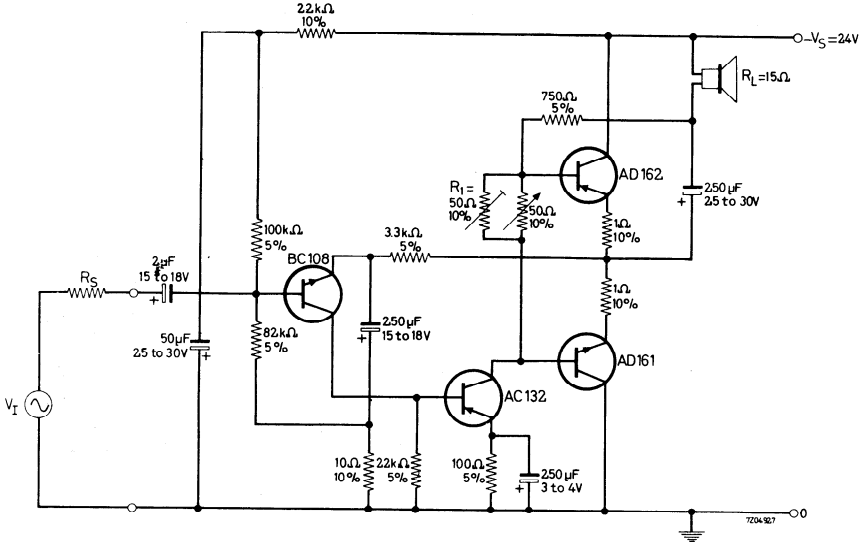
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Mica washer (50 to 100 μm)
and insulation bushes

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APPLICATION INFORMATION

4 W transformerless audio frequency amplifier with matched pair AD161/AD162 in complementary symmetry class B output stage.



Typical input requirements
for an output power of 4 W

$$V_i(\text{rms}) = 28 \text{ mV}; I_i(\text{rms}) = 0.7 \text{ } \mu\text{A};$$

$$R_i = 40 \text{ k}\Omega; T_{\text{amb max.}} = 45 \text{ } ^\circ\text{C}$$

Typical bandwidth (3 dB)

$$B = 70 \text{ Hz to } 16 \text{ kHz}$$

Quiescent current

$$I_{\text{CQ}} = 8 \text{ mA, adjustable with } R_1$$

Heatsink for AC132

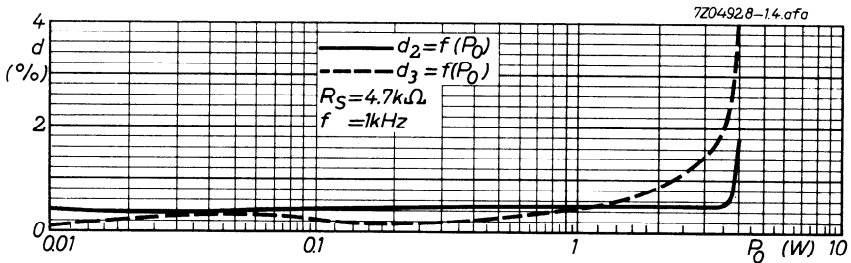
$$10 \text{ cm}^2 \text{ Al, thickness } 1 \text{ mm}$$

Heatsinks for AD161 and AD162

$$R_{\text{th h-a}} < 14.5 \text{ } ^\circ\text{C/W}$$

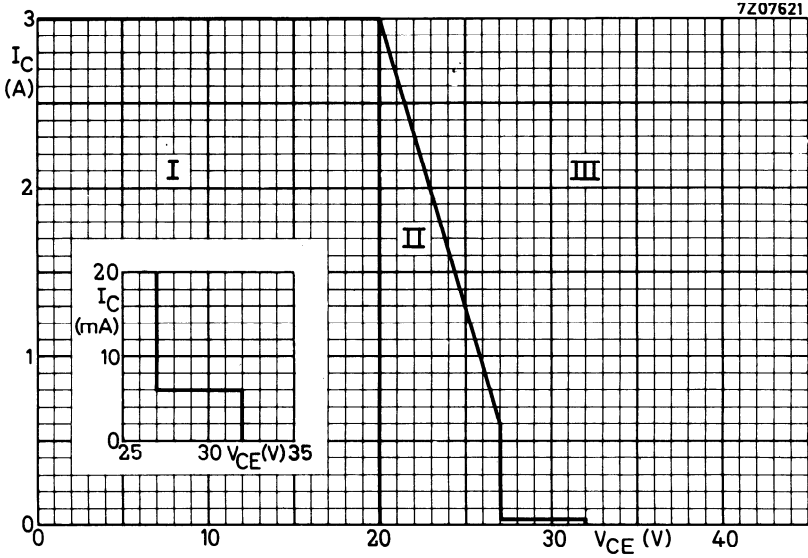
Supply voltage

$$-V_S = 24 \text{ V, max. } 27 \text{ V}$$

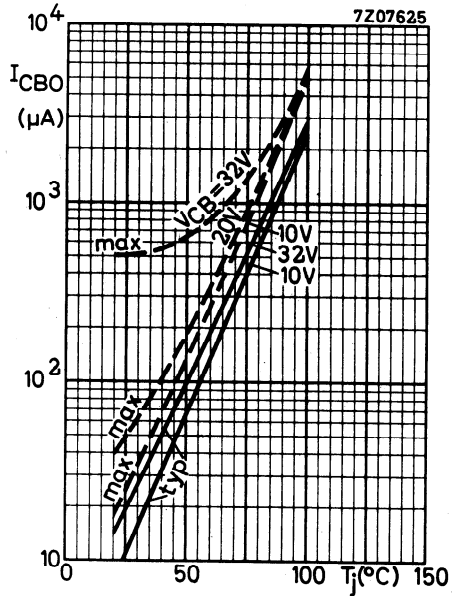
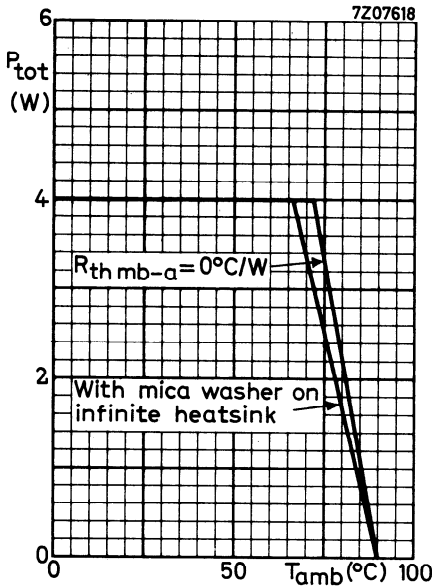
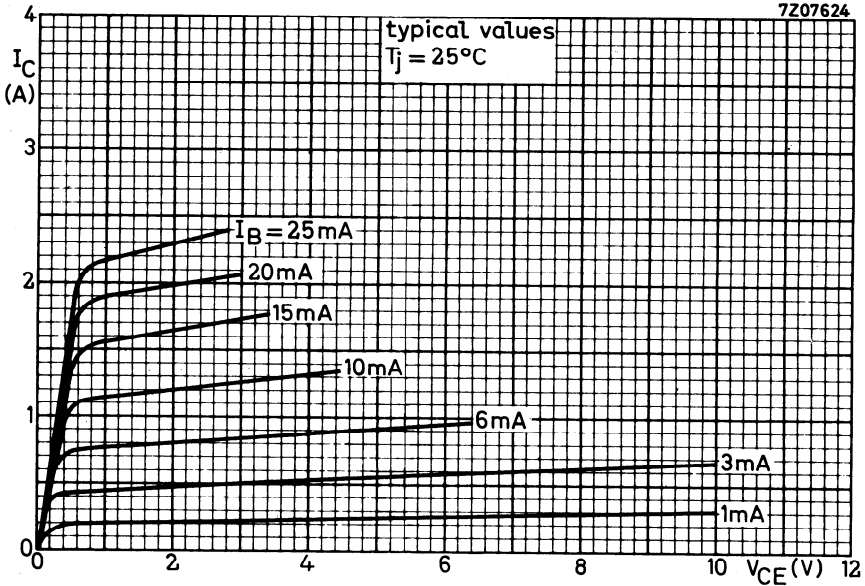


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AD161
AD161/AD162



- I = Region of permissible operation under all base-emitter conditions.
- II = Additional region of operation when the transistor is cut-off with $-V_{BE} \geq -V_{BEf1}$.
- III = Outside regions I and II, the transistor can withstand transient energies of 1 mWs, provided it is cut-off with $-V_{BB} \leq 0.6$ V; $R_i = 18 \Omega$.



AD161

AD161/AD162

